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**D-1449** APR 2 3 2002

TRADEMA

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO. MICRON.071DV1

APPLICATION NO. 10/060,842

RMATION DISCLOSURE STATEMENT **BY APPLICANT** 

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT Raina

FILING DATE January 29, 2002

GROUP 2877

EXAMINE	Р	DOCUMENTALINATES	T		<del></del> _	·	
INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE
in	1.	4,125,446	11/14/78	Hartsough et al.			(IF APPROPRIATE)
	2.	4,792,842	12/20/88	Honma et al.			<del></del>
	3.	5,147,819	09/15/92	Yu et al.			
$\perp$	4.	5,229,331	07/20/93	Doan et al.	<del></del>		
	5.	5,358,908	10/25/94	Reinberg et al.			
	6.	5,372,973	12/13/94	Doan et al.			
	7.	5,923,953	7/13/99	Goldenberg Barany et al.			
V	8.	6,154,188	11/28/00	Learn et al.			
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			FOREIGN PATENT DOCUMENTS				
EXAMINER INITIAL	DATE		COUNTRY	CLASS	SUBCLASS	TRANSLATION	
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EXAMINER INITIAL		OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
DA	9.	Takagi et al., "P2.2-3 Characterization of Al-Nd Alloy Thin Films for Interconnections of TFT-LCDs" Asia Display 1995, 4 pages.
gp	10.	Takayama et al., "Al-Sm and Al-Dy alloy thin films with low resistivity and high thermal stability for microelectronic conductor lines, Thin Solid Films 289, 1996 pp. 289-294.
ap	11.	Kim et al., "22.2 Pure Al and Al-Alloy Gate-Line Processes in TFT-LCDs", SID 96 Digest, pp. 337-340.
		SEA CIVE BITT

EXAMINER

DATE CONSIDERED 5/28/03 8 IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT O:\DOCS\LJM\LJM-1313.DOC:vb
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